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earlier application (Rule 4.17(iii))

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(54) Title: LAYER-LAYER ETCH OF NON VOLATILE MATERIALS

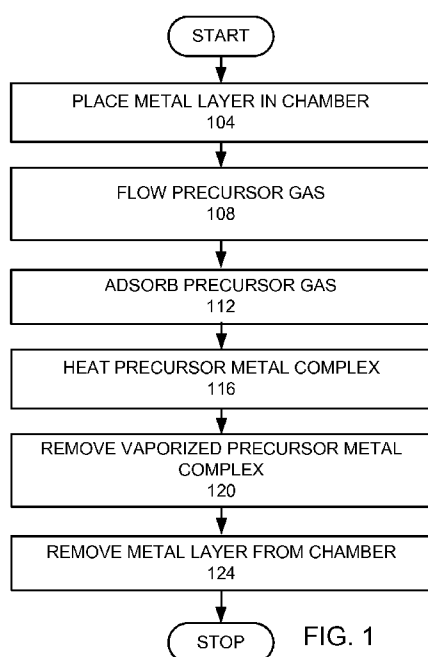


FIG. 1

(57) Abstract: A method for etching a metal layer disposed below a mask is provided. The metal layer is placed in an etch chamber. A precursor gas is flowed into the etch chamber. The precursor gas is adsorbed into the metal layer to form a precursor metal complex. The precursor metal complex is heated to a temperature above a vaporization temperature of the precursor metal complex, while the metal layer is exposed to the precursor gas. The vaporized precursor metal complex is exhausted from the etch chamber.



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